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Mi22-1534

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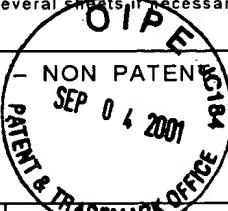
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TL		YING SHI ET AL., "Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics," 3 pages ( 1998).
TL		W.-H. LEE ET AL., "A Novel High-k Inter-Poly Dielectric (IPD), Al <sub>2</sub> O <sub>3</sub> for Low Voltage/High speed Flash Memories: Erasing in msec at 3.3V," p. 117-118, ( 1997).
TL		XIN GUO ET AL., "High Quality Ultra-thin (1.5 nm) TiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> Gate Dielectric for Deep Sub-micron CMOS technology," 4 pages, ( 1999).
TL		H.F. LUAN ET AL., "High quality Ta <sub>2</sub> O <sub>5</sub> gate dielectrics with T <sub>ox,eq</sub> <10 Å," 4 pages, (1999).
TL	v	K.J. HUBBARD <sup>a)</sup> ET AL., "Thermodynamic stability of binary oxides in contact with silicon," p. 2757-2776, ( 1996).
TL	v	B. CHENG ET AL., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100 nm MOSFET's," p. 1537-1544, (1999).
TL	q	C.T. LIU, "Circuit Requirement and Integration Challenges of Thin Gate Dielectrics for Ultra Small MOSFETs," 4 pages, ( 1998).
TL	s	B.H. LEE ET AL., "Ultrathin Hafnium Oxide with Low Leakage and Excellent Reliability for Alternative Gate Dielectric Application," 4 pages, ( 1999).
TL	w	S.P. MURARKA ET AL., "Thermal oxidation of hafnium silicide films on silicon," 3 pages, ( 1980).
TL	x	ALBERT CHIN ET AL., "High Quality La <sub>2</sub> O <sub>3</sub> and Al <sub>2</sub> O <sub>3</sub> Gate Dielectric with Equivalent Oxide Thickness 5-10Å," 2 pages, ( 2000).
TL	y	D.A. MULLER ET AL., "The electronic structure at the atomic scale of ultrathin gate oxides," 4 pages, ( 1999).
TL		Y. SAITO ET AL, "High-Integrity Silicon Oxide Grown at Low-Temperature by Atomic Oxygen Generated in High-Density Krypton Plasma," 2 pages, ( 1999).

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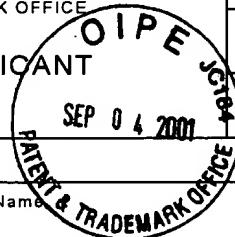
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## U.S. PATENT DOCUMENTS

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